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FDPF10N50FT N-Channel UniFETTM FRFET[®] MOSFET 500 V, 9 A, 850 mΩ

Features

- $R_{DS(on)}$ = 710 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 4.5 A
- Low Gate Charge (Typ. 18 nC)
- Low C_{rss} (Typ. 10 pF)
- 100% Avalanche Tested
- · Improved dv/dt Capability
- RoHS Compliant

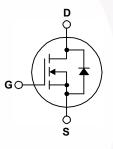
Applications

- LCD/LED/PDP TV
- Lighting
- Uninterruptible Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. The body diode's reverse recovery performance of UniFET FRFET[®] MOSFET has been enhanced by lifetime control. Its t_{rr} is less than 100nsec and the reverse dv/ dt immunity is 15V/ns while normal planar MOSFETs have over 200nsec and 4.5V/nsec respectively. Therefore, it can remove additional component and improve system reliability in certain applications in which the performance of MOSFET's body diode is significant. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Parameter		FDPF10N50FT	Unit	
Drain to Source Voltage		500	V	
Gate to Source Voltage			±30	V
I _D Drain Current	- Continuous (T _C = 25°C)	- Continuous (T _C = 25 ^o C)		
	- Continuous (T _C = 100°C	;)	5.4*	A
Drain Current	- Pulsed	(Note 1)	36*	А
Single Pulsed Avalanche Energy (Note 2)		364	mJ	
Avalanche Current (Note 1)		(Note 1)	9	А
Repetitive Avalanche Energy (Note 1)		(Note 1)	12.5	mJ
Peak Diode Recovery dv	/dt	(Note 3)	20	V/ns
P _D Power Dissipation	(T _C = 25 ^o C)		42	W
	- Derate Above 25°C		0.33	W/ ^o C
Operating and Storage T	emperature Range		-55 to +150	°C
Maximum Lead Tempera	ture for Soldering, 1/8" from Case	for 5 Seconds	300	°C
	Gate to Source Voltage Grain Current Drain Current Single Pulsed Avalanche Avalanche Current Repetitive Avalanche En Peak Diode Recovery dw Power Dissipation Operating and Storage T	$\begin{array}{c} \mbox{Drain to Source Voltage} \\ \mbox{Gate to Source Voltage} \\ \mbox{Gate to Source Voltage} \\ \mbox{Drain Current} & - Continuous (T_C = 25^{\circ}C) \\ - Continuous (T_C = 100^{\circ}C) \\ - Continuous (T_C = 25^{\circ}C) \\ - Continuous (T_C = 25^$	$\begin{array}{c} \mbox{Drain to Source Voltage} & & & \\ \mbox{Gate to Source Voltage} & & & \\ \mbox{Gate to Source Voltage} & & & \\ \mbox{Drain Current} & & & \\ \mbox{Drain Current} & & & \\ \mbox{Cc} = 25^{\circ}\text{C}) & & \\ \mbox{-continuous} (T_{C} = 25^{\circ}\text{C}) & & \\ \mbox{-continuous} (T_{C} = 100^{\circ}\text{C}) & & \\ \mbox{-continuous} (T_{C} = 100^{\circ}\text{C}) & & \\ \mbox{Drain Current} & & & \\ \mbox{Pulsed Avalanche Energy} & & & \\ \mbox{Note 1}) & & \\ \mbox{Repetitive Avalanche Energy} & & & \\ \mbox{Note 1}) & & \\ \mbox{Peak Diode Recovery dv/dt} & & & \\ \mbox{Power Dissipation} & & \\ \mbox{T}_{C} = 25^{\circ}\text{C}) & & \\ \mbox{-Derate Above 25^{\circ}\text{C}} & & \\ \end{tabular}$	$ \begin{array}{c c c c c c } \hline Drain to Source Voltage & 500 \\ \hline Gate to Source Voltage & \pm 30 \\ \hline Gate to Source Voltage & & & & & \\ \hline Gate to Source Voltage & & & & & \\ \hline Gate to Source Voltage & & & & & \\ \hline Gate to Source Voltage & & & & & \\ \hline Drain Current & & & & \\ \hline Drain Current & & & & & \\ \hline Drain Current & & & & & \\ \hline Pulsed & (Note 1) & & & & \\ \hline Single Pulsed Avalanche Energy & & & & \\ \hline Avalanche Current & & & & & \\ \hline Avalanche Current & & & & & \\ \hline Avalanche Current & & & & & \\ \hline Avalanche Current & & & & & \\ \hline Avalanche Current & & & & & \\ \hline Peak Diode Recovery dv/dt & & & & \\ \hline Power Dissipation & & & \\ \hline \hline C_{C} = 25^{\circ}C) & & & & \\ \hline Power Dissipation & & & \\ \hline Operating and Storage Temperature Range & & & \\ \hline \end{array} $

*Drain current limited by maximum junction temperature.

Thermal Characteristics

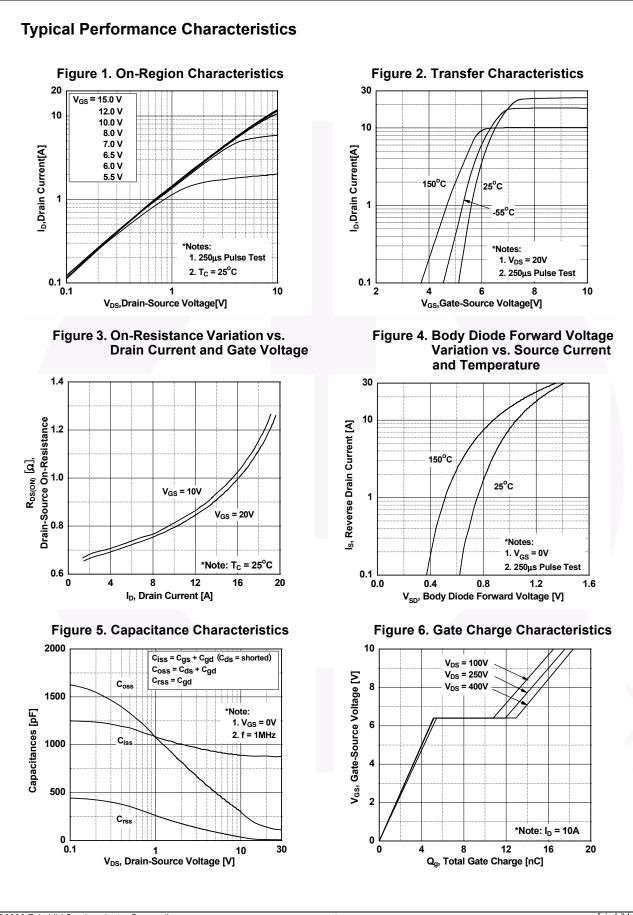
Symbol	Parameter	FDPF10N50FT	Unit	
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	3.0	°C/W	
R_{\thetaJA}	Thermal Resistance, Junction to Ambient, Max.	62.5	62.5	

November 2013

FT FDPF10N50FT Characteristics T _C = Parameter Fistics rain to Source Breakdown Vor reakdown Voltage Temperatu	25°C unl		Packing Method Tube rwise noted. Test Conditions	N/A s	Min.	ape Width N/A Typ.	50 Max.	units
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	_	$V_{DD} = 250 \text{ V}, \text{ I}_{D} = 10 \text{ A},$ $V_{CS} = 10 \text{ V}, \text{ R}_{C} = 25 \Omega$		-	-		ns	
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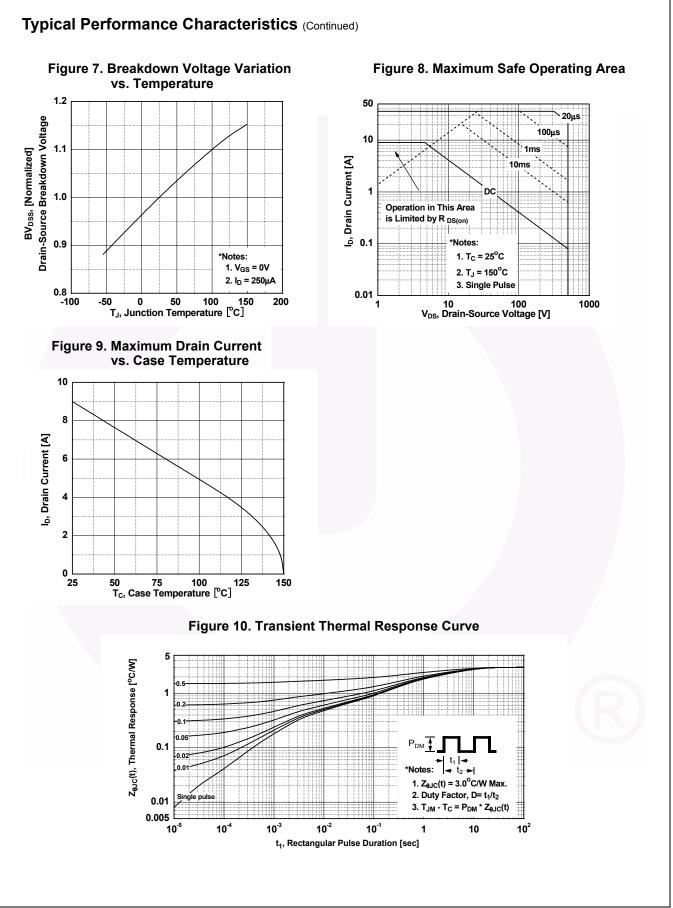
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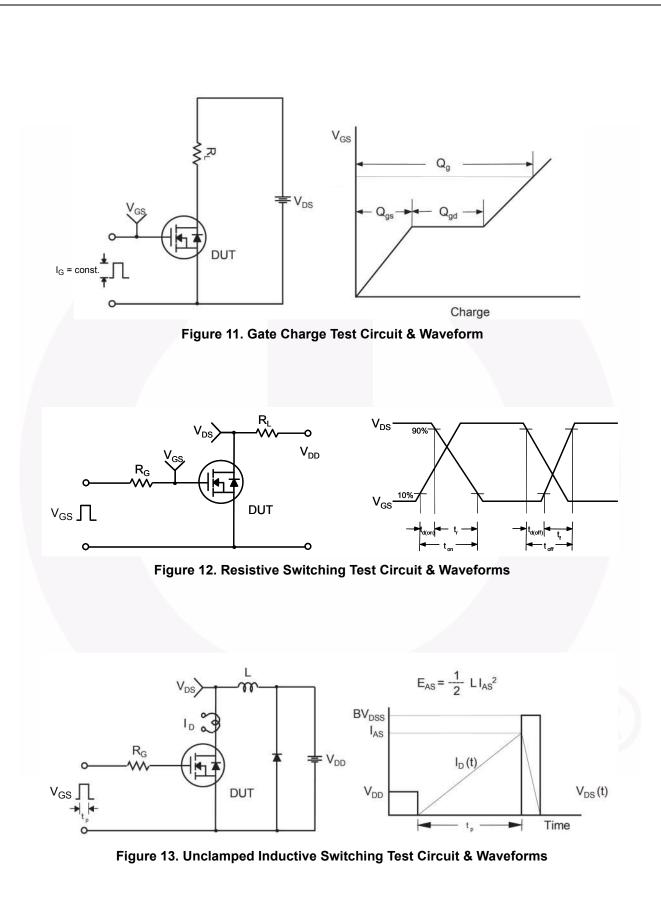
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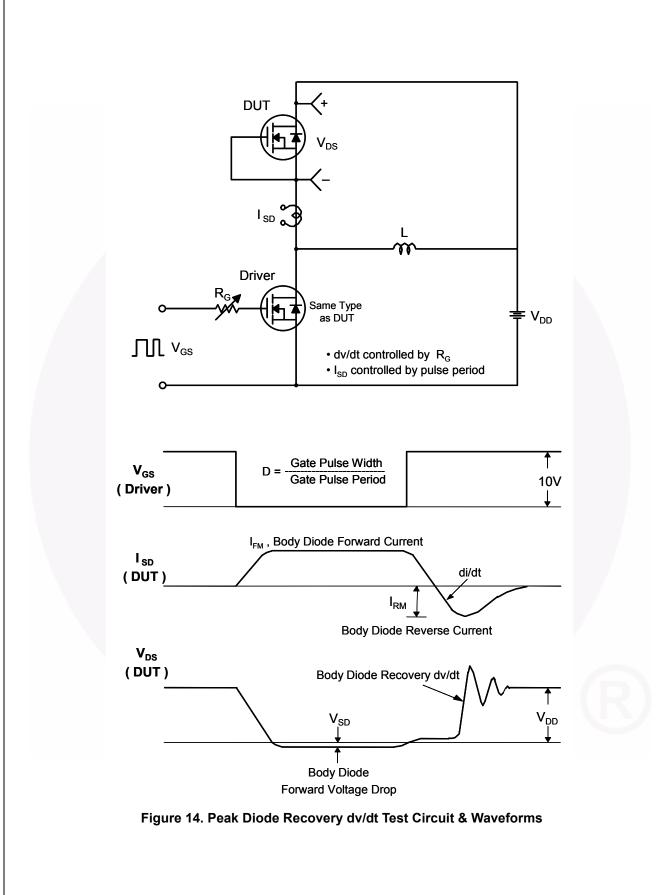
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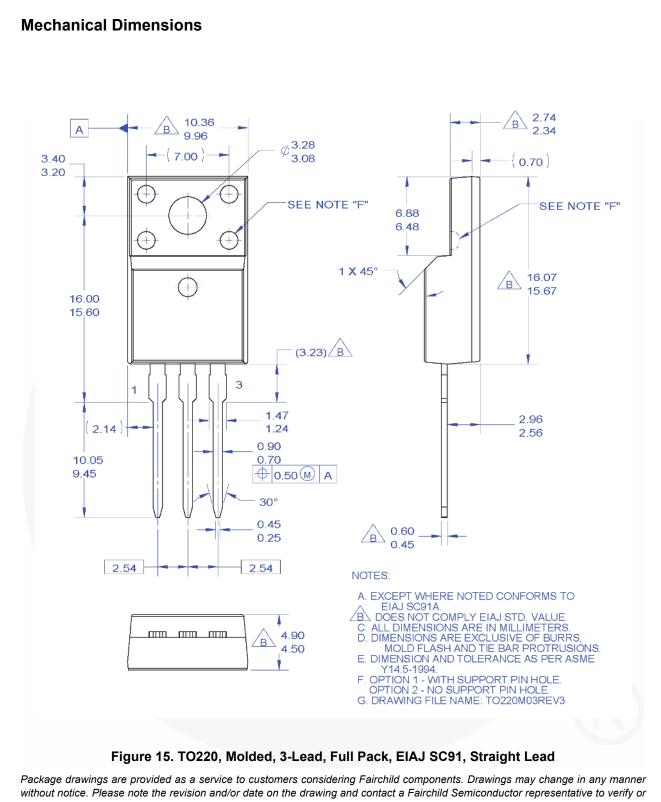


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